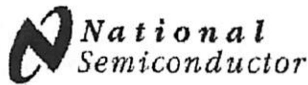
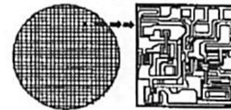


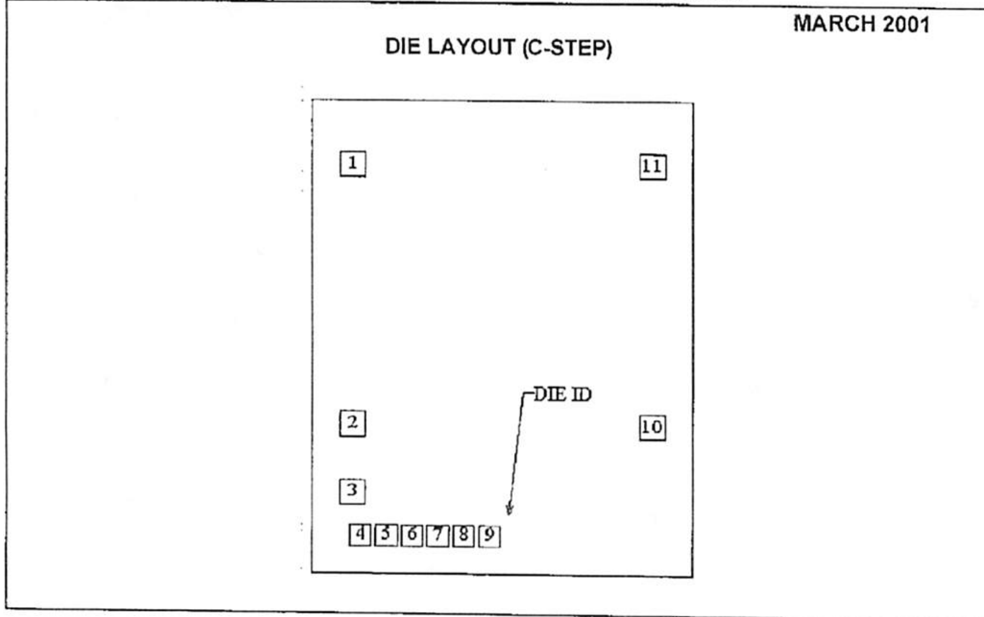
DPBU Die Datasheet



LMC6061 MDC MWC
DIE PRODUCT
PRECISION CMOS SINGLE MICROPOWER OPERATIONAL AMPLIFIER

MARCH 2001

DIE LAYOUT (C-STEP)



DIE/WAFER CHARACTERISTICS

Fabrication Attributes		General Die Information	
Physical Die Identification	LMC6061C	Bond Pad Opening Size (min)	92µm x 92µm
Die Step	C	Bond Pad Metalization	ALUMINUM
Physical Attributes		Passivation	VOM NITRIDE
Wafer Diameter	150mm	Back Side Metal	BARE BACK
Die Size (Drawn)	1397µm x 1753µm 55mils x 69mils	Back Side Bias	Floating
Thickness	330µm Nominal		
Min Pitch	254µm Nominal		

Special Assembly Requirements:

Note: Actual die size is rounded to the nearest micron.

Die Bond Pad Coordinate Locations (C -Step)
(Referenced to die center, coordinates in µm) NC = No Connection

SIGNAL NAME	PAD# NUMBER	X/Y CORRDINATES X	Y	PAD SIZE X		Y
INPUT -	1	-552	638	92	x	92
INPUT +	2	-552	-326	92	x	92
V-	3	-552	-580	92	x	92
NC	4	-523	-736	78	x	78
NC	5	-428	-736	78	x	78
NC	6	-334	-736	78	x	78
NC	7	-239	-736	78	x	78
NC	8	-144	-736	78	x	78
NC	9	-48	-736	78	x	78
OUTPUT	10	552	-326	92	x	92
V+	11	552	638	92	x	92

LEXIS-NEXIS LEXIS-NEXIS LEXIS-NEXIS